

FIG 1

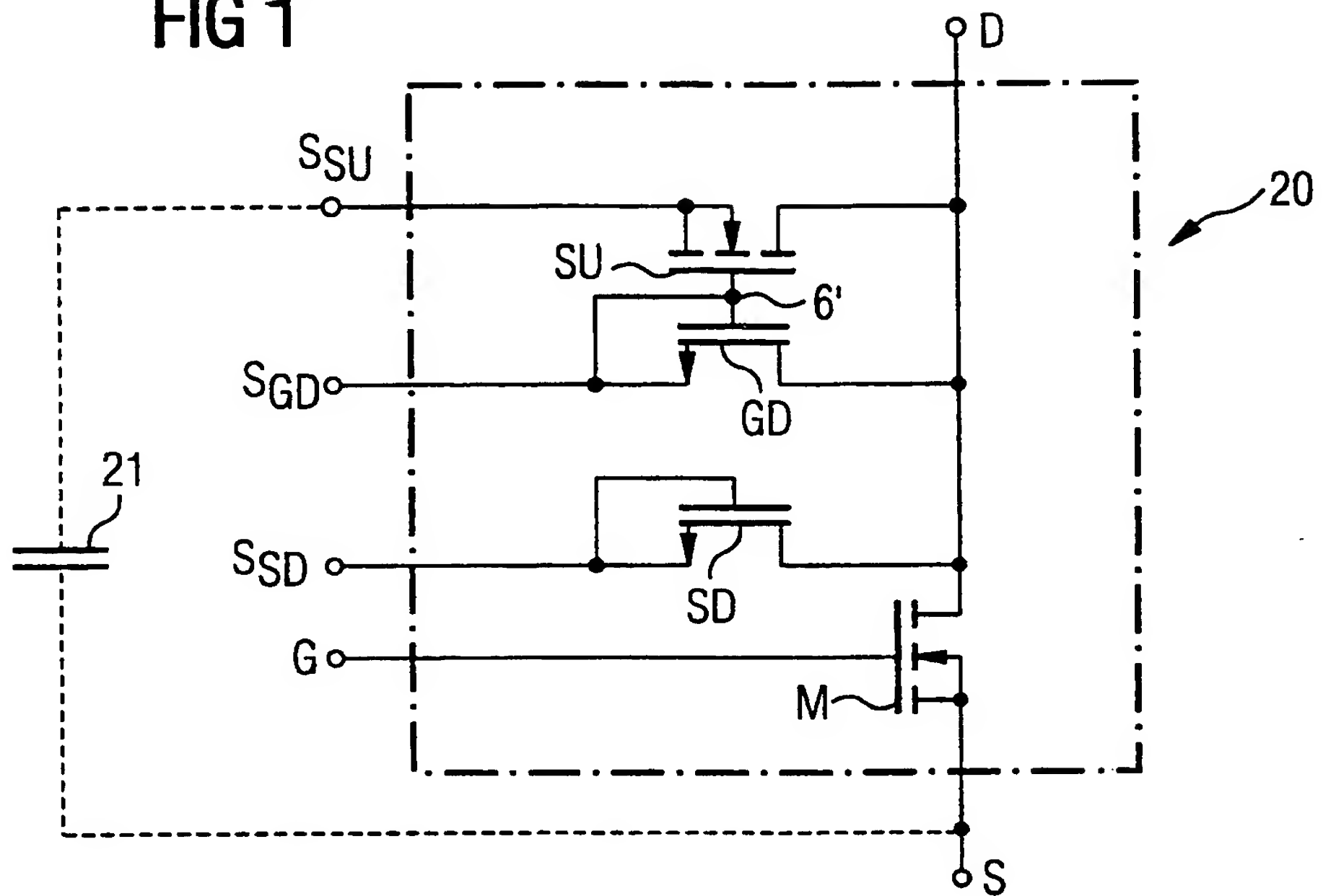


FIG 3

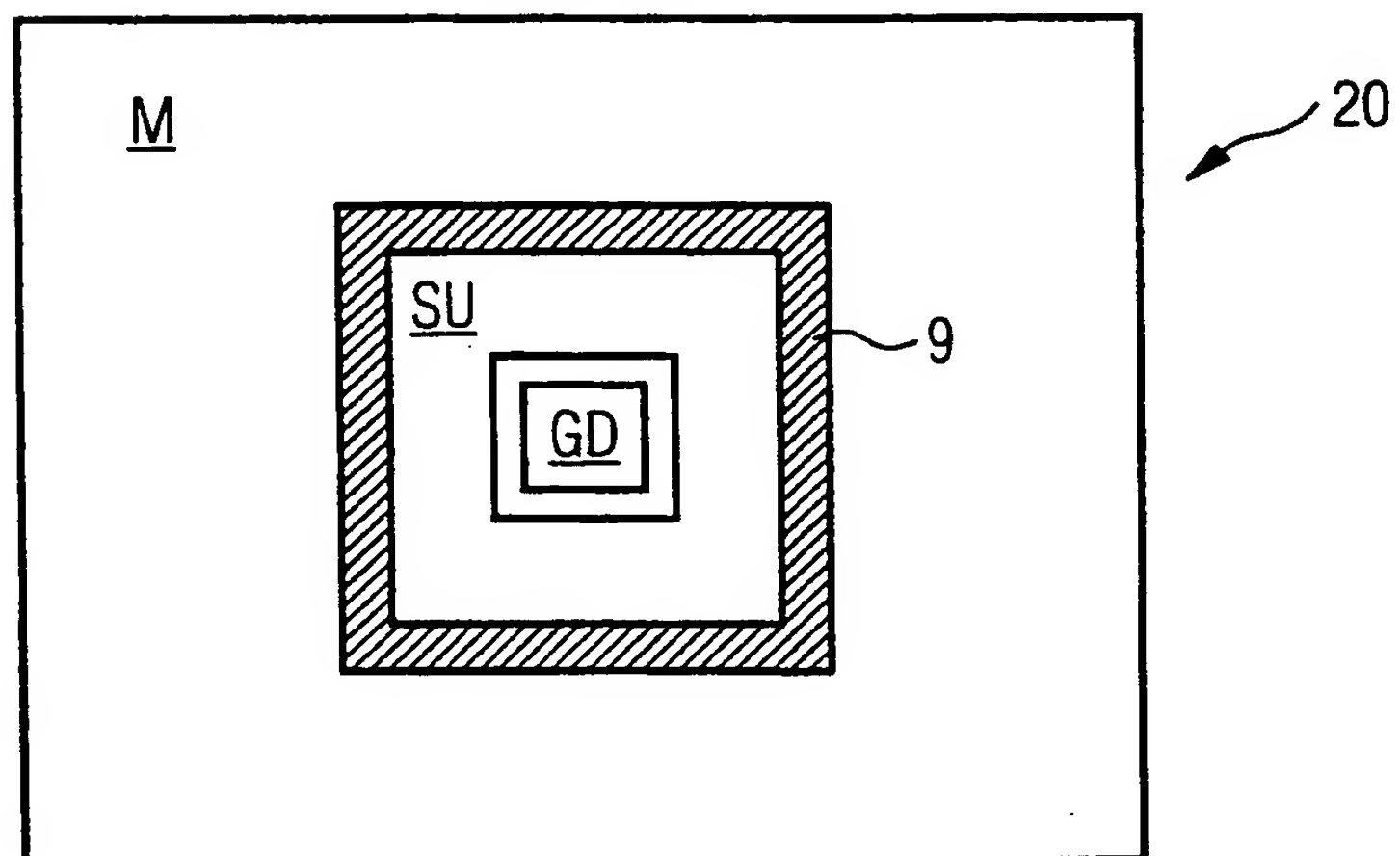


FIG. 2 is a cross-sectional view of a semiconductor device, taken along the line II-II of FIG. 1, showing the internal structure of the device, including the gate oxide layer, the gate electrodes, the channel region, the source and drain regions, and the interconnects.

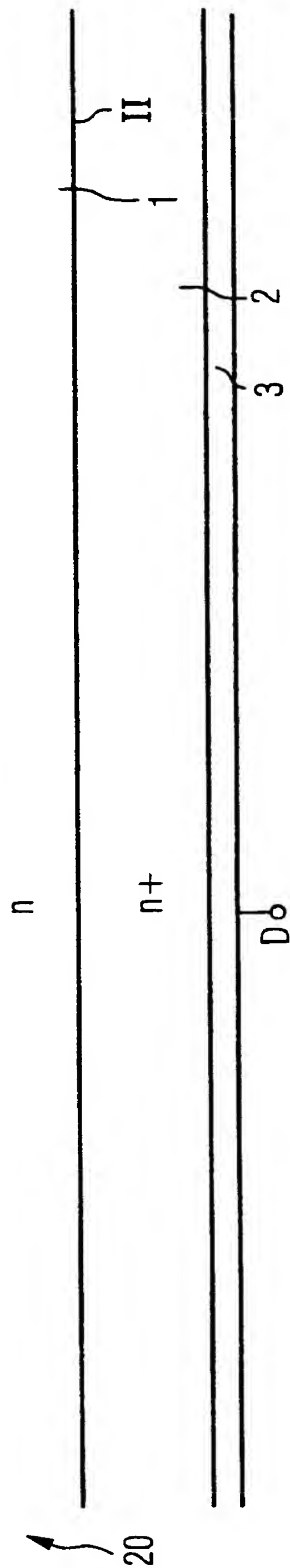
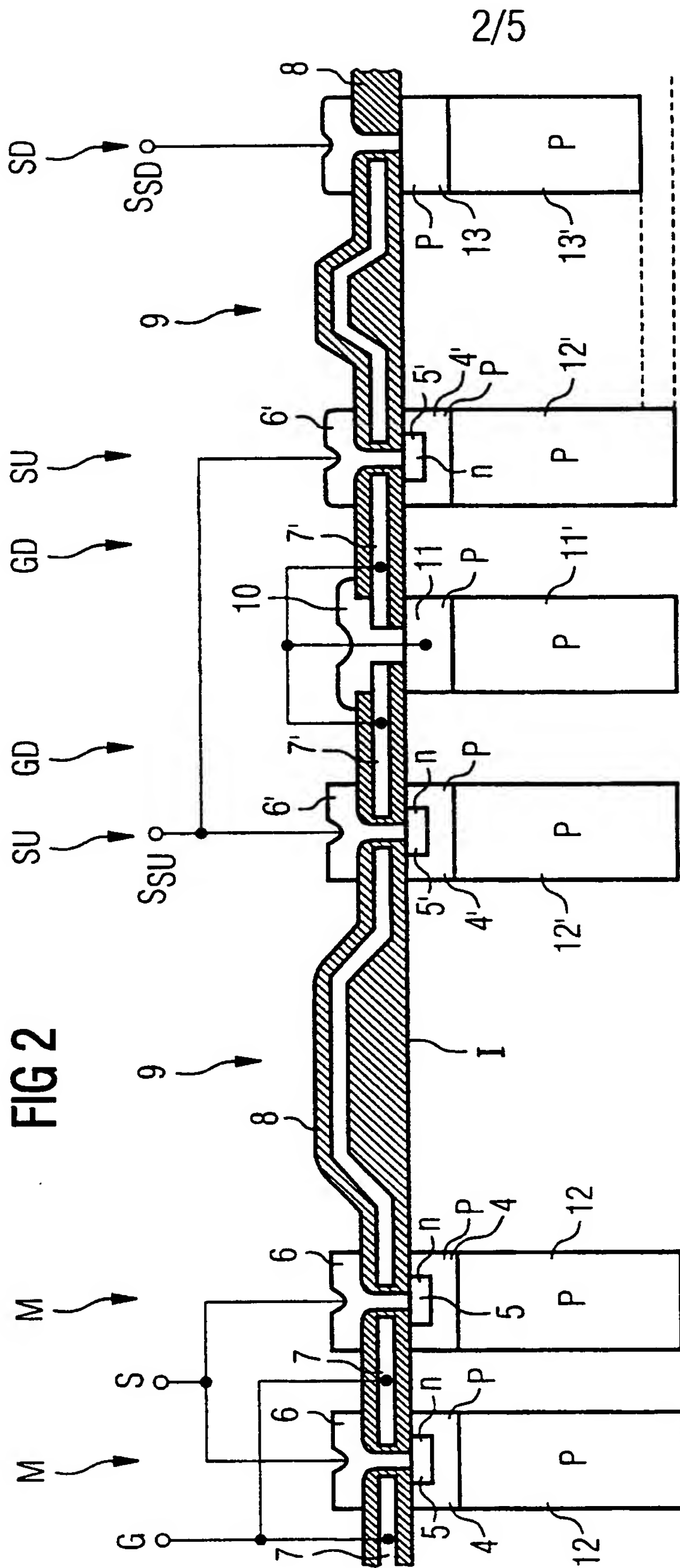


FIG 4

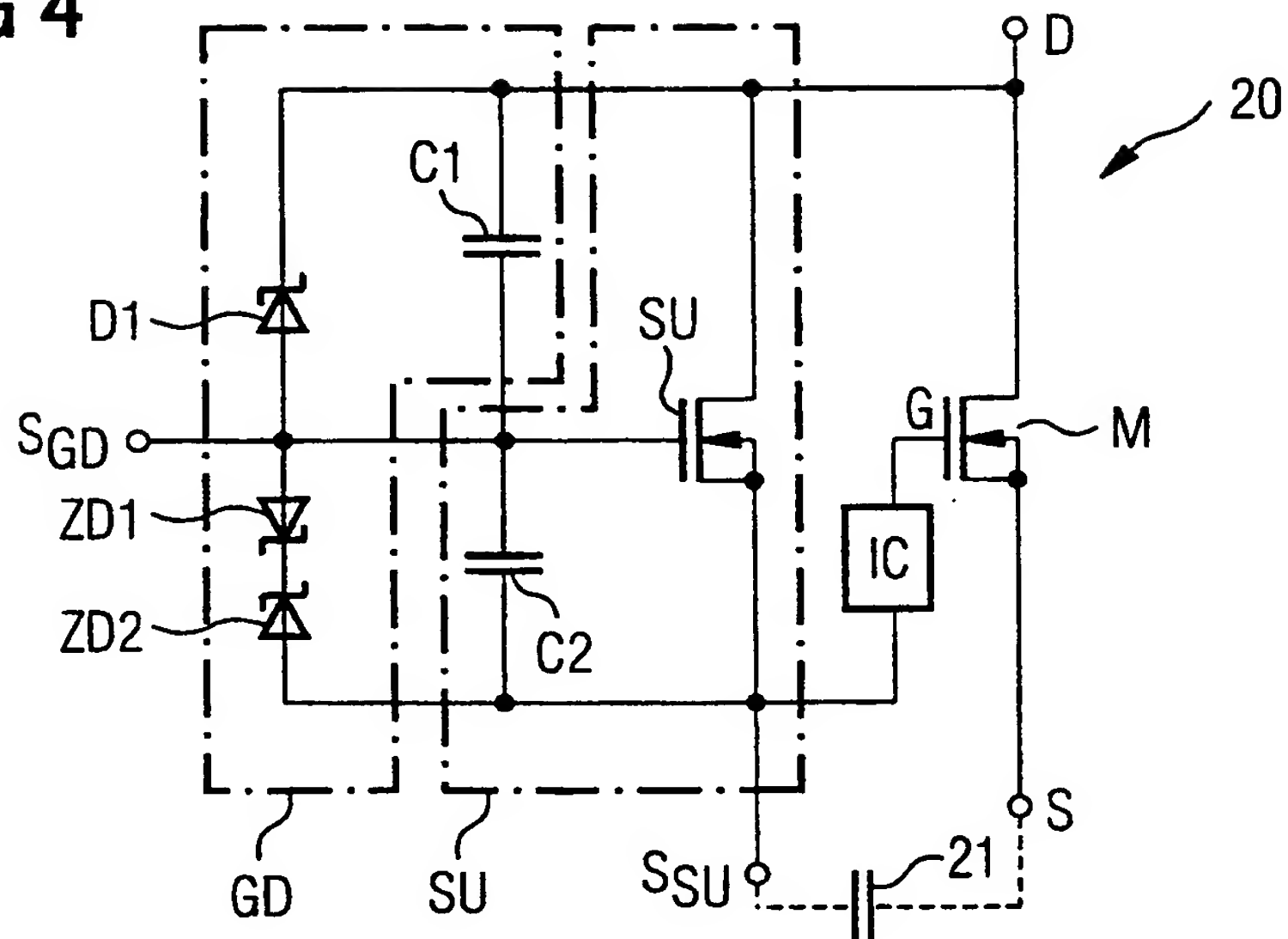


FIG 5

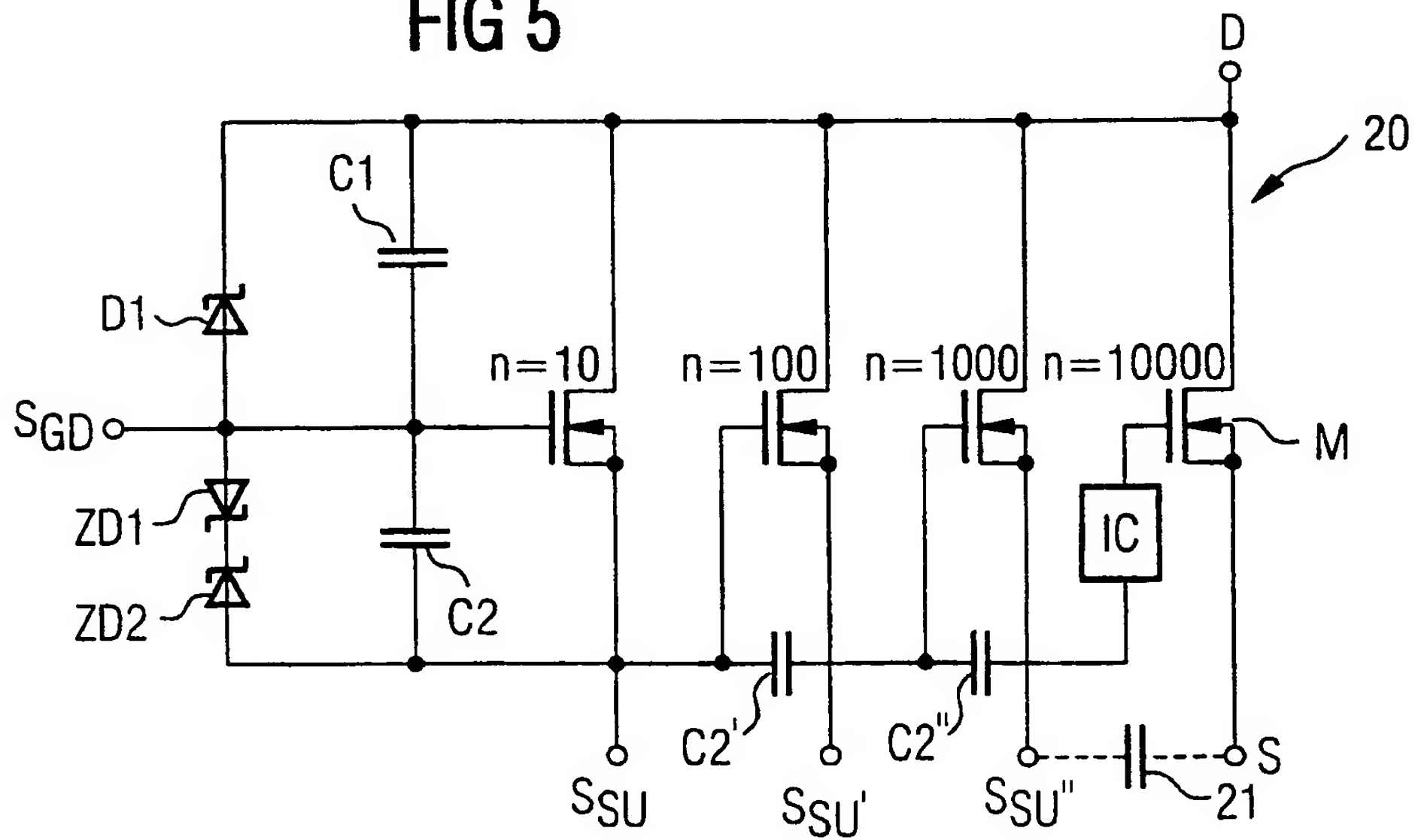


FIG 6

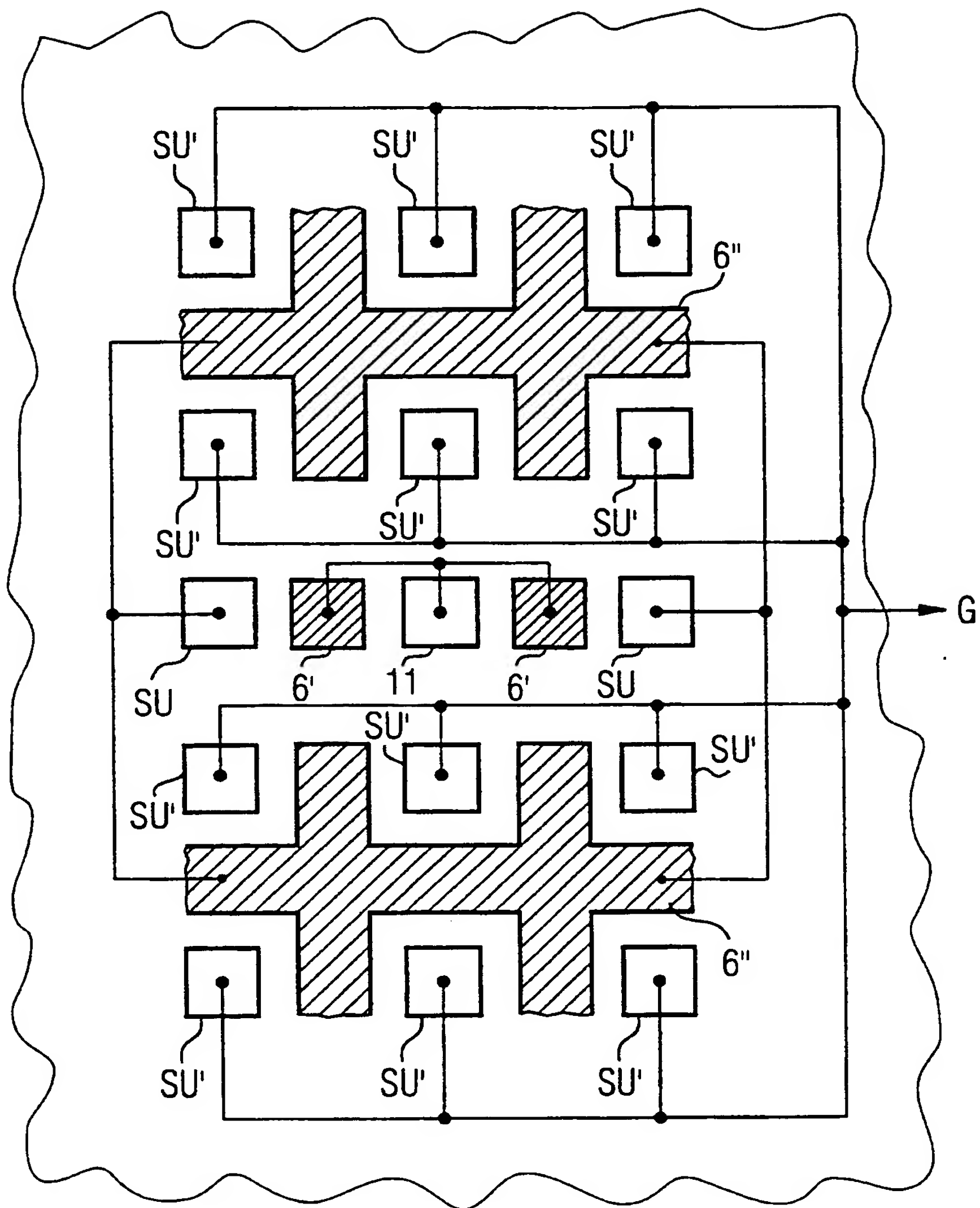


FIG. 7 is a cross-sectional view of a semiconductor device, taken along line I-I of FIG. 6, showing the internal structure of the device, including the substrate, the gate, the source, the drain, and the interconnects.

FIG 7

